

**AMENDMENTS TO THE CLAIMS**

1. (Original) A lithographic projection apparatus comprising:  
a radiation system to provide a projection beam of radiation;  
a support structure to support a patterning structure to pattern the projection beam according to a desired pattern;  
a substrate table to hold a substrate;  
a projection system to project the patterned beam onto a target portion of the substrate;  
a vibrationally isolated reference frame;  
at least one position sensor constructed and arranged to monitor a position of at least one of the patterning structure and substrate mounted on the reference frame; and  
at least one temperature control member operatively associated with at least one component selected from a group comprising said support structure, said substrate table, said projection system and said isolated reference frame and comprising a substantially absorption and emission-inhibiting surface finish such that said at least one component is maintained substantially isothermal during operation.

2. (New) An apparatus according to claim 1, wherein said absorption and emission-inhibiting surface finish comprises a substantially mirror-like surface finish.

3. (New) An apparatus according to claim 1, wherein an emission coefficient of said absorption and emission-inhibiting surface finish is less than 0.1.

4. (New) An apparatus according to claim 3, wherein said emission coefficient of said absorption and emission-inhibiting surface finish is less than 0.05.

5. (New) An apparatus according to claim 1, wherein the apparatus further comprises a chamber substantially enclosing at least one component selected from said group.

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6. (New) An apparatus according to claim 5, wherein at least part of a surface of the temperature control member which faces towards at least one component selected from said group and a heat source internal of said chamber comprises a substantially absorption and emission-promoting surface finish.

7. (New) An apparatus according to claim 6, wherein said absorption and emission-promoting surface finish comprises a black surface finish.

8. (New) An apparatus according to claim 6, wherein an emission coefficient of said absorption and emission-promoting surface finish is at least 0.9.

9. (New) An apparatus according to claim 6, wherein said emission coefficient of said absorption and emission-promoting surface finish is at least 0.95.

10. (New) An apparatus according to claim 1, wherein a surface of said temperature control member which comprises said absorption and emission-inhibiting surface finish faces towards a heat source external of a space that is at least partially surrounded by said temperature control member and that comprises said component.

11. (New) An apparatus according to claim 1, wherein a thermal conductivity of a material of said temperature control member is at least 100 W/mK.

12. (New) An apparatus according to claim 1, wherein said temperature control member comprises a material selected from the group comprising aluminum, aluminum alloys, copper and copper alloys.

13. (New) An apparatus according to claim 5, wherein said temperature control member is at least partially formed by walls of said chamber.

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14. (New) An apparatus according to claim 1, wherein said temperature control member comprises an enclosure provided at a distance from a wall of said chamber.
15. (New) An apparatus according to claim 1, wherein the support structure comprises a mask table for holding a mask.
16. (New) An apparatus according to claim 1, wherein the radiation system comprises a radiation source.
17. (New) An apparatus according to claim 5, wherein said chamber is a vacuum chamber.
18. (New) An apparatus according to claim 17, wherein said temperature control member comprises a wall of a thermal baffle provided over an opening to a pump, in particular a vacuum pump.
19. (New) An apparatus according to claim 1, wherein said projection beam comprises EUV radiation having a wavelength in the range of 5 to 20 nm.
20. (New) A device manufacturing method comprising:  
projecting a patterned beam of radiation onto a target portion of a layer of radiation-sensitive material on a substrate; and maintaining a substantially isothermal condition in a component provided in a lithographic projection apparatus using at least one temperature control member at least partially surrounding the component, said temperature control member being at least partially formed of a material having an absorption and emission inhibiting surface finish.
21. (New) A device manufactured according to the method of claim 20.